

Silicon Carbide Diode 31 August 2018

Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A(TO-220AC) plastic package, designed for high frequency switched-mode power supplies

2. Features and benefits

- Highly stable switching performance
- High forward surge capability IFSM
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	$\delta = 0.5$; T _{mb} \leq 105 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	-	16	A
Static chara	acteristics			·		
V _F	forward voltage	I _F = 16 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V

Silicon Carbide Diode

5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K – K – A
2	А	anode	$2 \circ \zeta$	001aaa020
mb	mb	mounting base; connected to cathode	O U U U U U U U U U U U U U U U U U U U	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
NXPSC16650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A			

NXPSC16650

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 105 °C; square-wave pulse; <u>Fig. 1; Fig. 2; Fig. 3; Fig. 4</u>	-	16	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $$; t_p = 25 $\mu s;$ square-wave pulse	-	32	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN	-	96	А
	forward current	t _p = 10 μs; T _{j(init)} = 25 °C; SIN	-	770	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

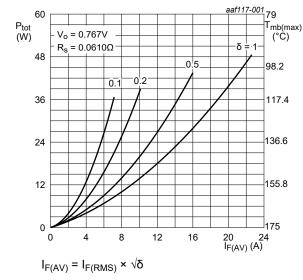
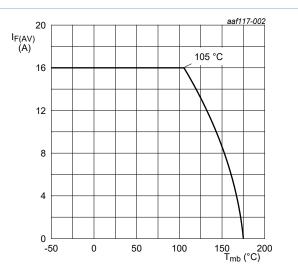


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

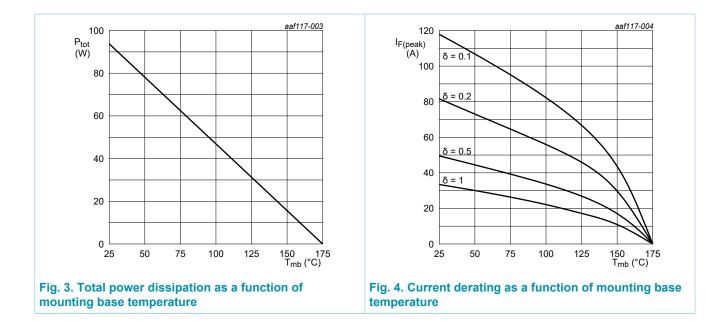




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NXPSC16650

Silicon Carbide Diode

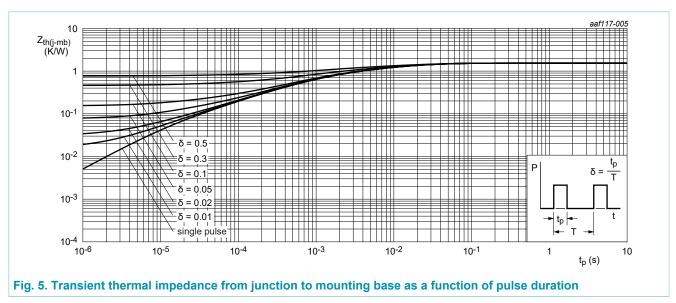


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Silicon Carbide Diode

8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	1.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



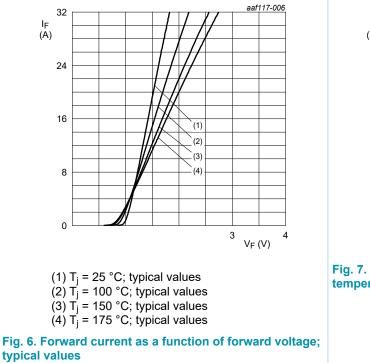
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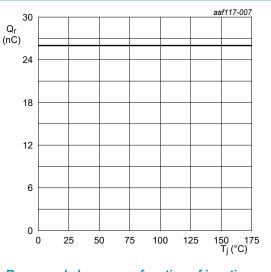
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9. Characteristics

Symbol	Parameter	Conditions	Mi	ו Typ	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 16 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 16 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	100	μA
		V _R = 650 V; T _j = 150 °C	-	-	400	μA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·		·		
Q _r	recovered charge	$I_F = 16 \text{ A}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $V_R = 400 \text{ V}; T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	26	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	534	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	75	-	pF
		f = 1 MHz; V _R = 600 V; T _i = 25 °C	-	73	-	pF









Silicon Carbide Diode

10. Package outline

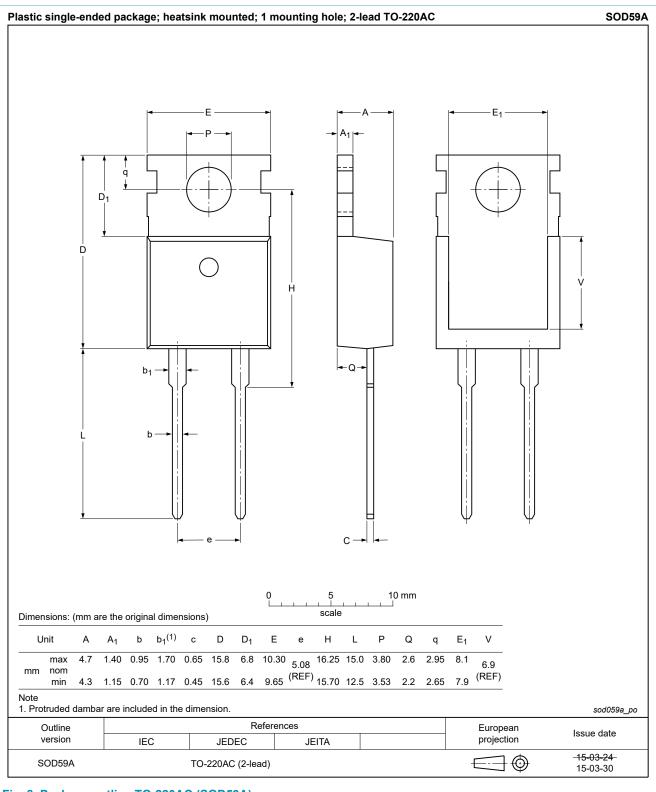


Fig. 8. Package outline TO-220AC (SOD59A)

NXPSC16650

Silicon Carbide Diode

11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Silicon Carbide Diode

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NXPSC16650

12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	. 3
8.	Thermal characteristics	. 5
9.	Characteristics	6
10	Package outline	7
11.	Legal information	. 8

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